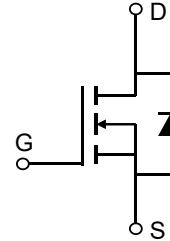


Description

Features

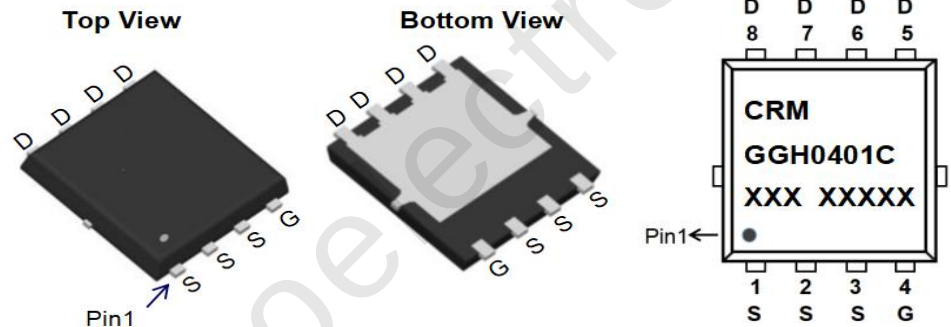
- 40V, 285A
 $R_{DS(ON)}$ Typ = 0.7mΩ @ $V_{GS} = 10V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_d s TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMGGH0401C	CRMGGH0401C	PDFN5x6-8L	TAPING	13"	5000	60000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	285
		$T_C = 100^\circ\text{C}$	171
I_{DM}	Pulsed Drain Current ⁽¹⁾	1140	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	841	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	125
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.3	2.8	3.4	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	-	0.7	0.9	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V},$ $f = 1\text{MHz}$	-	5344	-	pF
C_{oss}	Output Capacitance		-	2363	-	pF
C_{rss}	Reverse Transfer Capacitance		-	200	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 20\text{V}, I_D = 30\text{A}$	-	75	-	nC
Q_{gs}	Gate Source Charge		-	19	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	17.5	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 20\text{V}$ $I_D = 30\text{A}, R_{GEN} = 1.6\Omega$	-	8.5	-	ns
t_r	Turn-On Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	52	-	ns
t_f	Turn-Off Fall Time		-	12	-	ns

Drain-Source Diode Characteristics and Max Ratings

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	285	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	1140	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 30A, di/dt = 100A/us	-	22	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	40	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 20\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 58\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

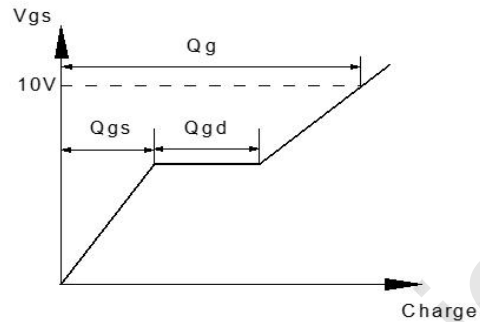
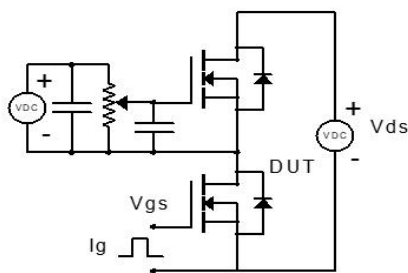


Figure 1: Gate Charge Test Circuit & Waveform

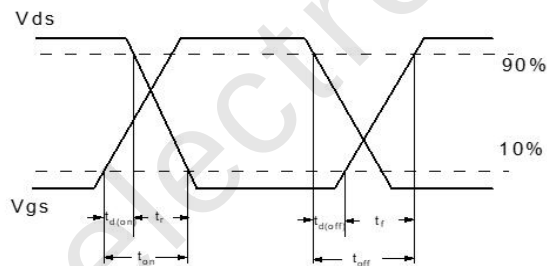
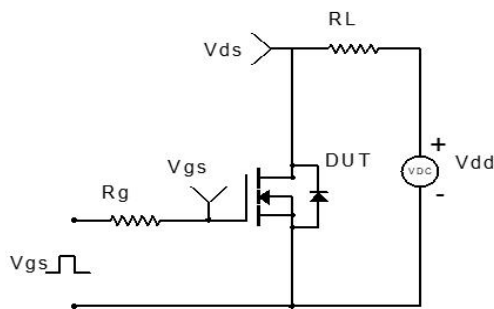


Figure 2: Resistive Switching Test Circuit & Waveform

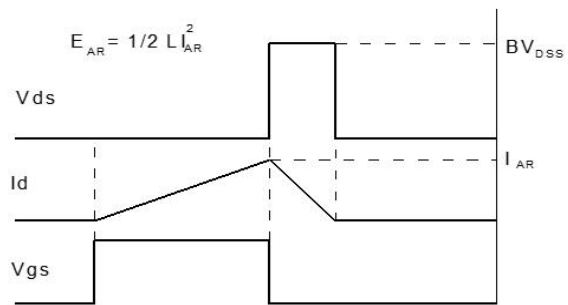
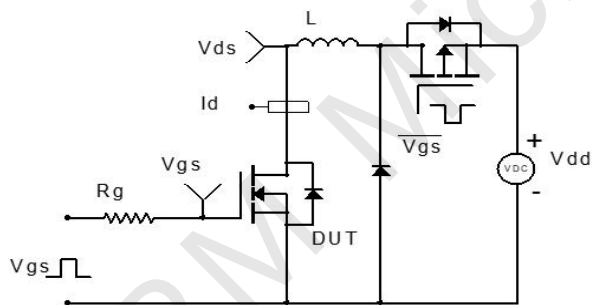


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

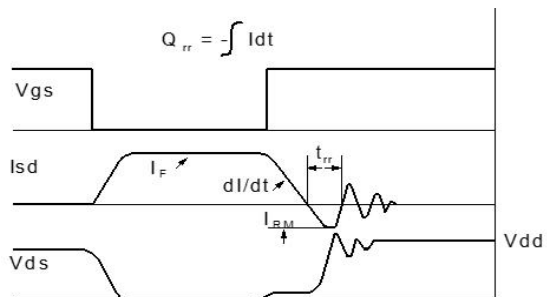
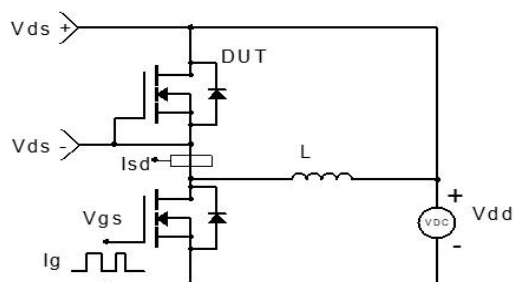
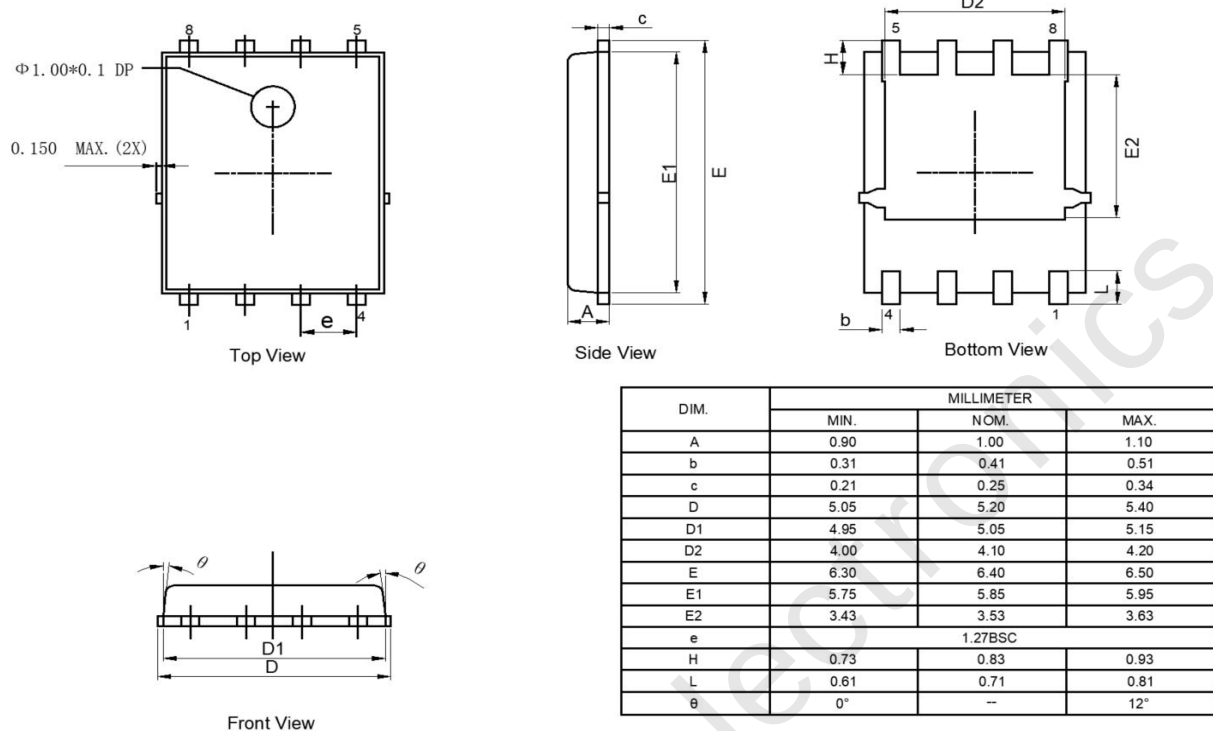


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN5x6-8L)



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